

Operational Amplifier

Low Noise High Output Drive Rail-to-Rail input/output CMOS Operational Amplifier

TLR2374FV-LB

General Description

This product is a rank product for the industrial equipment market.

This is the best product for use in these applications.

This product is a Rail-to-Rail input/output monolithic IC integrated quad independent CMOS operational amplifier features wide operating voltage range with 4 V to 16 V, low input offset voltage, low noise, low input bias current and high output drive. It is suitable for equipment operating from battery power and using sensors that an amplifier.

Features

- Low Noise
- Rail-to-Rail input/output
- Wide Operating Supply Voltage Range
- High Output Drive

Applications

- Industrial Equipment
- Battery-powered Equipment
- Current Monitoring Amplifier
- ADC Front Ends, Buffer Amplifier
- Photodiode Amplifiers
- Sensor Amplifiers

Key Specifications

■ Input Offset Voltage: 1.5 mV (Max)

■ Input-referred Noise Voltage Density

f = 1 kHz: 25 nV/ $\sqrt{\text{Hz}}$ (Typ) f = 10 kHz: 12 nV/ $\sqrt{\text{Hz}}$ (Typ)

■ Common-mode Input Voltage Range:

V_{SS} to V_{DD}

■ Input Bias Current: 2.5 pA (Typ)

■ Output Current (V_{OUT} = 0.5 V): 22 mA (Typ)

Operating Supply Voltage Range

Single Supply: 4.0 V to 16.0 V

Dual Supply: ±2.0 V to ±8.0 V

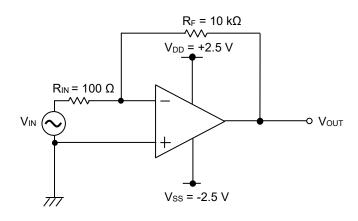
■ Operating Temperature Range: -40 °C to +125 °C

Package SSOP-B14

W (Typ) x D (Typ) x H (Max) 5.0 mm x 6.4 mm x 1.35 mm

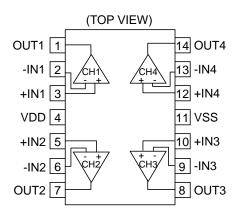


Typical Application Circuit



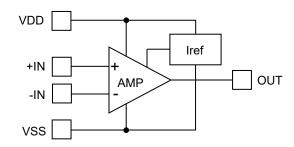
$$V_{OUT} = -\frac{R_F}{R_{IN}} V_{IN}$$

Pin Configurations



Pin No.	Pin Name	Function
1	OUT1	Output1
2	-IN1	Inverting input1
3	+IN1	Non-inverting input1
4	VDD	Positive power supply
5	+IN2	Non-inverting input2
6	-IN2	Inverting input2
7	OUT2	Output2
8	OUT3	Output3
9	-IN3	Inverting input3
10	+IN3	Non-inverting input3
11	VSS	Negative power supply / Ground
12	+IN4	Non-inverting input4
13	-IN4	Inverting input4
14	OUT4	Output4

Block Diagram



(Note) Each channel has the same configuration.

Description of Blocks

1. AMP:

This block is a full-swing output operational amplifier with class-AB output circuit and high-precision-Rail-to-Rail differential input stage.

2. Iref:

This block supplies reference current which is needed to operate AMP block.

Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Rating	Unit
Supply Voltage (V _{DD} - V _{SS})	Vs	18	V
Input Pin Voltage (+IN, -IN)	Vı	(Vss - 0.3) to (Vss + 18)	V
Input Pin Current (+IN, -IN)	l _l	10	mA
Maximum Junction Temperature	Tjmax	150	ů
Storage Temperature Range	Tstg	-55 to +150	°C

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operate over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

Thermal Resistance(Note 1)

Parameter		Thermal Res	l lmit		
Parameter	Symbol	1s ^(Note 3)	2s2p ^(Note 4)	Unit	
SSOP-B14					
Junction to Ambient	θја	159.6	92.8	°C/W	
Junction to Top Characterization Parameter ^(Note 2)	Ψ_{JT}	13	9	°C/W	

⁽Note 1) Based on JESD51-2A(Still-Air).

(Note 4) Using a PCB board based on JESD51-7.

Layer Number of Measurement Board	Material	Board Size			
Single	FR-4	114.3 mm x 76.2 mm x	1.57 mmt		
Тор					
Copper Pattern	Thickness				
Footprints and Traces	70 µm				
Layer Number of Measurement Board	Material	Board Size			
4 Layers	FR-4	114.3 mm x 76.2 mm	x 1.6 mmt		
Тор		2 Internal Laye	ers	Bottom	
Copper Pattern	Thickness	Copper Pattern	Thickness	Copper Pattern	Thickness
Footprints and Traces	70 µm	74.2 mm x 74.2 mm	35 µm	74.2 mm x 74.2 mm	70 µm

Recommended Operating Conditions

offinionate operating contained							
Parameter	Symbol	Min	Тур	Max	Unit		
Supply Voltage (V V)	Single Supply	Vs	4.0	5.0	16.0	V	
Supply Voltage (V _{DD} - V _{SS})	Dual Supply	VS	±2.0	±2.5	±8.0		
Operating Temperature		Topr	-40	+25	+125	°C	

⁽Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

⁽Note 3) Using a PCB board based on JESD51-3.

Electrical Characteristics

(Unless otherwise specified V_S = 5 V, V_{SS} = 0 V, V_{ICM} = 2.5 V, R_L = 10 k Ω to V_{ICM} , Ta = 25 °C)

Input Offset Voltage	Limit		Linit	Conditions			
Input Offset Voltage	Parameter	Symbol	Min	Тур	Max	Unit	Conditions
1.50		.,	-	0.01	0.60	.,,	No load, Absolute value
Temperature Drift ΔV(0/Δ1) - 0.2 7.0 μV C Ta = -40 °C to +125 °C Input Offset Current Ilo - 0 - pA Absolute value Input Bias Current Ila - 2.5 - pA Absolute value Common-mode Input Voltage Range VicMR 0 - 5 V Vss to Vpo Supply Current Ibo - 4.5 6.8 mA No load, G = 0 dB. No load, G = 0 dB. Ta = -40 °C to +125 °C Output Voltage High VoH - 20 100 mV IL = 1 mA, VoH = Vpo - VoUT Output Voltage High VoL - 20 100 mV IL = 1 mA, VoH = Vpo - VoUT Output Voltage Low VoL - 20 100 mV IL = 1 mA, VoH = Vpo - VoUT Output Source Current (Note: 2) Ion - 22 - mA Vour = Vpo - 0.5 V, Absolute value Output Sink Current (Note: 2) Ion - 22 - mA Vour = Vpo - 0.5 V, Absolute value <td>Input Offset Voltage</td> <td>Vio</td> <td>-</td> <td>-</td> <td>1.50</td> <td>mV</td> <td></td>	Input Offset Voltage	Vio	-	-	1.50	mV	
Input Bias Current Input Voltage Range Victure Victure Victor Victor		ΔV10/ΔΤ	-	0.2	7.0	μV/°C	
Common-mode Input Voltage Range V _{ICMR} 0 - 5 V Vss to V _{DD} Supply Current I _{DD} - 4.5 6.8 mA No load, G = 0 dB Output Voltage High - 20 100 mV IL = 1 mA, V _{OH} = V _{DD} - V _{OUT} , Ta = -40 °C to +125 °C Output Voltage Low - 20 100 mV IL = 1 mA, V _{OH} = V _{DD} - V _{OUT} , Ta = -40 °C to +125 °C Output Source Current (Noter 1) IoH - 22 mA V _{OUT} = V _{DD} - 0.5 V, Absolute value Output Sink Current (Noter 1) IoH - 22 mA V _{OUT} = V _{SS} + 0.5 V, Absolute value Output Sink Current (Noter 1) IoL - 22 mA V _{OUT} = V _{SS} + 0.5 V, Absolute value Cutput Signal Voltage Gain Av 82 110 - dB - Large Signal Voltage Gain Av 82 110 - dB - Base Margin θ - 65 - MHz G = 40 dB, CL = 25 pF Common-mode Rejection Ratio CMRR	Input Offset Current	lio	-	0	-	pA	Absolute value
Range No load, G = 0 dB Ta = -40 °C to +125 °C	Input Bias Current	lΒ	-	2.5	-	pA	Absolute value
Supply Current IDD - - 7 mA No load, G = 0 dB, Ta = -40 °C to +125 °C Output Voltage High VoH - 20 100 mV IL = 1 mA, VoH = VoD - VoUT Output Voltage Low VoL - 20 100 mV IL = 1 mA, VoH = VoD - VOUT, Ta = -40 °C to +125 °C Output Voltage Low VoL - 20 100 mV IL = 1 mA, VoH = VoD - VOUT, Ta = -40 °C to +125 °C Output Source Current (Note 1) IoH - 22 - mA VouT = VoD - 0.5 V, Absolute value Output Sink Current (Note 1) IoL - 22 - mA VouT = Vss + 0.5 V, Absolute value Output Sink Current (Note 1) IoL - 22 - mA VouT = Vss + 0.5 V, Absolute value Output Sink Current (Note 1) IoL - 22 - mA VouT = Vss + 0.5 V, Absolute value Large Signal Voltage Gain Av 82 110 - dB - Phase Margin θ - 65 - MHz G =		V _{ICMR}	0	-	5	V	V _{SS} to V _{DD}
Output Voltage High VoH Ta = -40 °C to +125 °C			-	4.5	6.8		No load, G = 0 dB
Output Voltage High VoH - - 150 mV IL = 1 mA, VoH = VoD - VoUT, Ta = -40 °C to +125 °C Output Voltage Low VoL - 20 100 mV IL = 1 mA, VoH = VoD - VoUT, Ta = -40 °C to +125 °C Output Source Current (Note 1) IoH - 22 - mA VouT = VoD - 0.5 V, Absolute value Output Sink Current (Note 1) IoL - 22 - mA VouT = VoD - 0.5 V, Absolute value Large Signal Voltage Gain Av 82 110 - dB - Large Signal Voltage Gain Av 82 110 - dB - Bandwidth Product GBW - 5 - MHz G = 40 dB, CL = 25 pF Calin Bandwidth Product GBW - 65 - deg G = 40 dB, CL = 25 pF Phase Margin θ - 65 - dB - Common-mode Rejection Ratio CMRR 70 90 - dB - Slew Rate SR	Supply Current	IDD	-	-	7	mA mA	
Coutput Voltage Low IL = 1 mA,		.,	-	20	100	.,	I _L = 1 mA, V _{OH} = V _{DD} - V _{OUT}
Output Voltage Low Vol. - - 150 mV IL = 1 mA, Ta = -40 °C to +125 °C Output Source Current (Note 1) IoH - 22 - mA Vour = Vpp - 0.5 V, Absolute value Output Sink Current (Note 1) IoL - 22 - mA Vour = Vss + 0.5 V, Absolute value Large Signal Voltage Gain Av 82 110 - dB - Rain Bandwidth Product GBW - 5 - MHz G = 40 dB, CL = 25 pF Phase Margin θ - 65 - deg G = 40 dB, CL = 25 pF Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs CL = 50 pF Input-referred Noise Voltage Density - 25 - nV/-Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N -	Output Voltage High	Vон	-	-	150	mV	I _L = 1 mA, V _{OH} = V _{DD} - V _{OUT} , Ta = -40 °C to +125 °C
Coutput Source Current (Note 1) IoH - 22 - mA Vout = Vout - 0.5 V, Absolute value			-	20	100		I _L = 1 mA,
Output Sink Current (Note 1) I _{OL} - 22 - mA V _{OUT} = V _{SS} + 0.5 V, Absolute value Large Signal Voltage Gain Av 82 110 - dB - Ta = -40 °C to +125 °C Gain Bandwidth Product GBW - 5 - MHz G = 40 dB, C _L = 25 pF Phase Margin θ - 65 - deg G = 40 dB, C _L = 25 pF Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs C _L = 50 pF Input-referred Noise Voltage Density - 25 - nV/-Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.0001 - % Vout = 2.5 Vp-p, f = 1 kHz	Output Voltage Low	Vol	-	-	150	mV	
Large Signal Voltage Gain Av 82 110 - dB - Ta = -40 °C to +125 °C Gain Bandwidth Product GBW - 5 - MHz G = 40 dB, CL = 25 pF Phase Margin θ - 65 - deg G = 40 dB, CL = 25 pF Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs CL = 50 pF Input-referred Noise Voltage Density Vn - 25 - nV/\Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vour = 2.5 Vp-p, f = 1 kHz	Output Source Current (Note 1)	Іон	-	22	-	mA	V _{OUT} = V _{DD} - 0.5 V, Absolute value
Large Signal Voltage Gain Av 80 - - dB Ta = -40 °C to +125 °C Gain Bandwidth Product GBW - 5 - MHz G = 40 dB, C _L = 25 pF Phase Margin θ - 65 - deg G = 40 dB, C _L = 25 pF Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs C _L = 50 pF Input-referred Noise Voltage Density Vn - 25 - nV/√Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vout = 2.5 Vp-p, f = 1 kHz	Output Sink Current (Note 1)	I _{OL}	-	22	-	mA	V _{OUT} = V _{SS} + 0.5 V, Absolute value
Gain Bandwidth Product GBW - - - MHz G = 40 dB, CL = 25 pF Phase Margin θ - 65 - deg G = 40 dB, CL = 25 pF Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs CL = 50 pF Input-referred Noise Voltage Density - 25 - nV/√Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vour = 2.5 Vp-p, f = 1 kHz	Laura Cirra IIValla va Caira		82	110	-	-ID	-
Phase Margin θ - 65 - deg G = 40 dB, C _L = 25 pF Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs C _L = 50 pF Input-referred Noise Voltage Density Vn - 25 - nV/√Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vout = 2.5 Vp-p, f = 1 kHz	Large Signal Voltage Gain	Av	80	-	-	gB	Ta = -40 °C to +125 °C
Common-mode Rejection Ratio CMRR 70 90 - dB - Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs C _L = 50 pF Input-referred Noise Voltage Density Vn - 25 - nV/√Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vout = 2.5 Vp-p, f = 1 kHz	Gain Bandwidth Product	GBW	-	5	-	MHz	G = 40 dB, C _L = 25 pF
Power Supply Rejection Ratio PSRR 70 90 - dB - Slew Rate SR - 3 - V/μs C _L = 50 pF Input-referred Noise Voltage Density - 25 - nV/√Hz f = 1 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vouт = 2.5 Vp-p, f = 1 kHz	Phase Margin	θ	-	65	-	deg	G = 40 dB, C _L = 25 pF
Slew Rate SR - 3 - V/ μ s C _L = 50 pF Input-referred Noise Voltage Density - 25 - μ ThD+N - 0.001 - % Vout = 2.5 Vp-p, f = 1 kHz	Common-mode Rejection Ratio	CMRR	70	90	-	dB	-
Input-referred Noise Voltage Density $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Power Supply Rejection Ratio	PSRR	70	90	-	dB	-
Input-referred Noise Voltage Density $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Slew Rate	SR	-	3	-	V/µs	C _L = 50 pF
Density - 12 - 110 - 110 f = 10 kHz Total Harmonic Distortion + Noise THD+N - 0.001 - % Vout = 2.5 Vp-p, f = 1 kHz	Input-referred Noise Voltage	1/	-	25	-	->//:/ -	f = 1 kHz
Noise 1 HD+N - 0.001 - % VOUT = 2.5 Vp-p, T = 1 KHZ		vn	-	12	-	nv/VHZ	f = 10 kHz
Channel Separation CS - 100 - dB input referred		THD+N	-	0.001	-	%	V _{OUT} = 2.5 Vp-p, f = 1 kHz
	Channel Separation	cs	-	100	-	dB	input referred

⁽Note 1) Consider the power dissipation of the IC under high temperature environment when selecting the output current value. When the output pin is short-circuited continuously, the output current may decrease due to the temperature rise by the heat generation of inside the IC.

Typical Performance Curves

 $V_{SS} = 0 V$

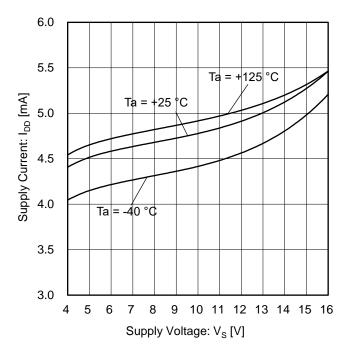


Figure 1. Supply Current vs Supply Voltage

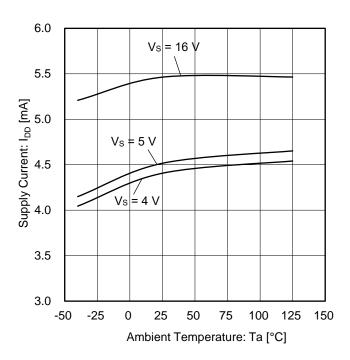


Figure 2. Supply Current vs Ambient Temperature

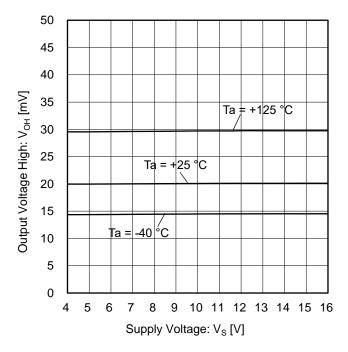


Figure 3. Output Voltage High vs Supply Voltage (I_L = 1 mA)

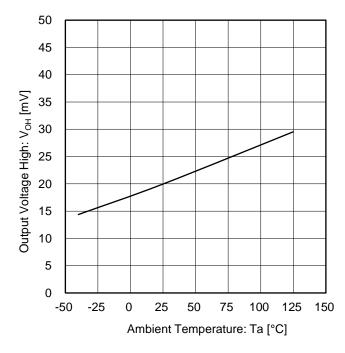


Figure 4. Output Voltage High vs Ambient Temperature $(V_S = 5 \text{ V}, I_L = 1 \text{ mA})$

 $V_{SS} = 0 V$

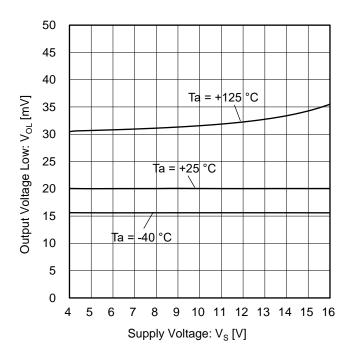


Figure 5. Output Voltage Low vs Supply Voltage (I∟ = 1 mA)

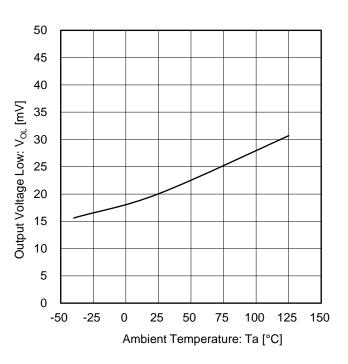


Figure 6. Output Voltage Low vs Ambient Temperature $(V_S = 5 \text{ V}, I_L = 1 \text{ mA})$

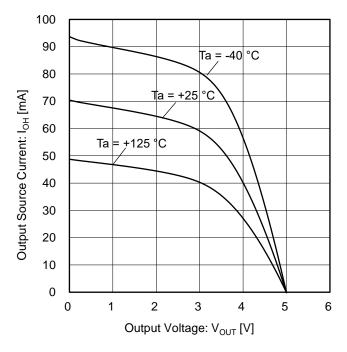


Figure 7. Output Source Current vs Output Voltage $(V_S = 5 V)$

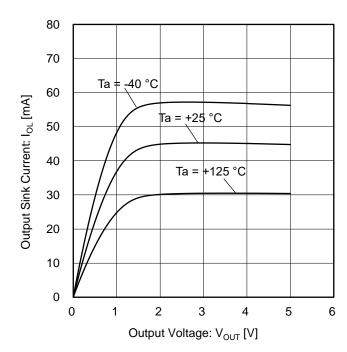
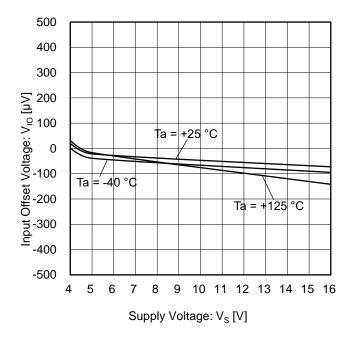


Figure 8. Output Sink Current vs Output Voltage $(V_S = 5 V)$

 $V_{SS} = 0 V$



500 400 300 $V_{s} = 4 V$ Vs = 5 V Vs = 16 V 400 -500 -50 -25 0 25 50 75 100 125 150 Ambient Temperature: Ta [°C]

Figure 9. Input Offset Voltage vs Supply Voltage

Figure 10. Input Offset Voltage vs Ambient Temperature

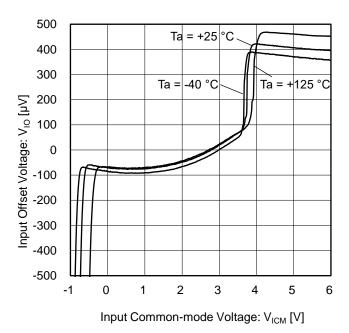


Figure 11. Input Offset Voltage vs Input Common-mode Voltage $(V_S = 5 V)$

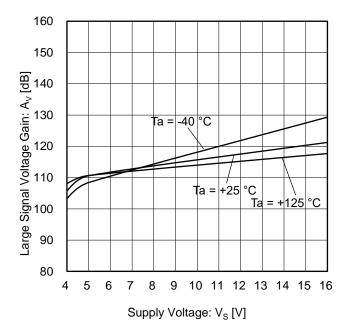
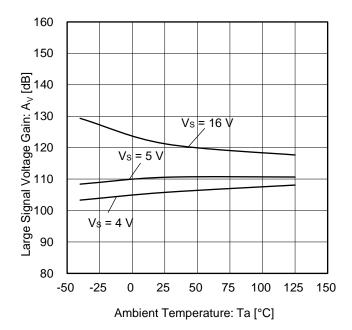


Figure 12. Large Signal Voltage Gain vs Supply Voltage ($R_L = 10 \text{ k}\Omega$)

 $V_{SS} = 0 V$



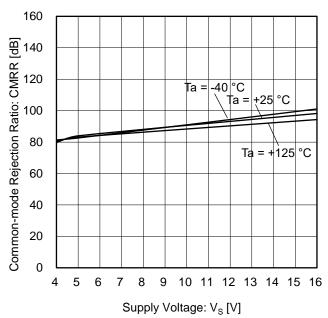
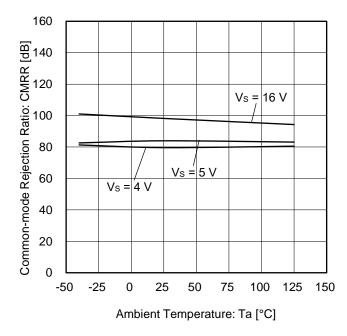


Figure 13. Large Signal Voltage Gain vs Ambient Temperature

Figure 14. Common-mode Rejection Ratio vs Supply Voltage





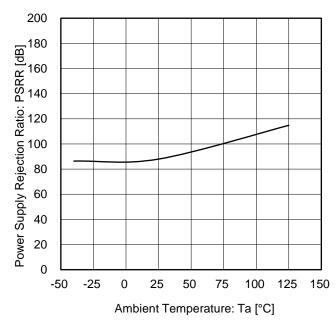
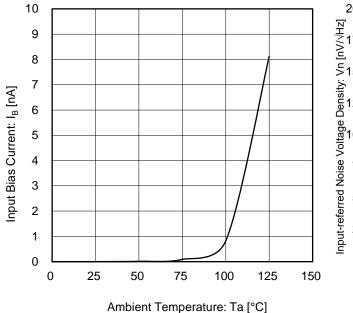


Figure 16. Power Supply Rejection Ratio vs Ambient Temperature

 $V_{SS} = 0 V$



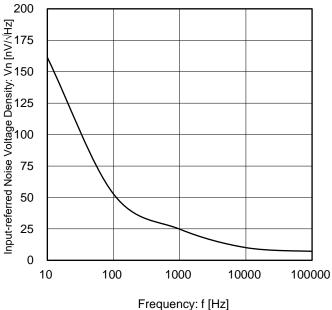


Figure 17. Input Bias Current vs Ambient Temperature (Vs = 5 V)

Figure 18. Input-referred Noise Voltage Density vs Frequency (Vs = 5 V)

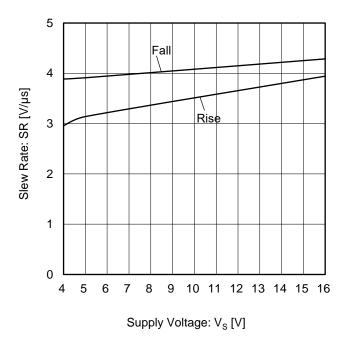


Figure 19. Slew Rate vs Supply Voltage

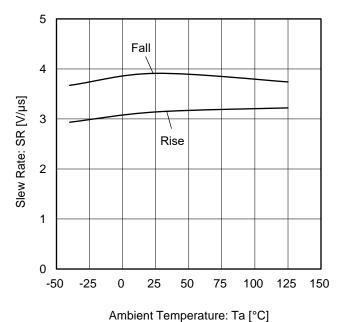


Figure 20. Slew Rate vs Ambient Temperature (Vs = 5 V)

 $V_{SS} = 0 V$

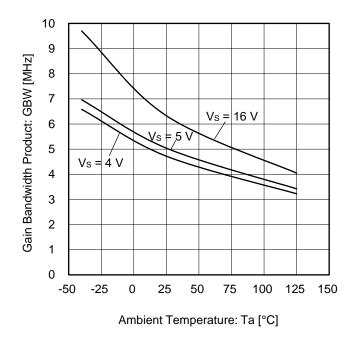
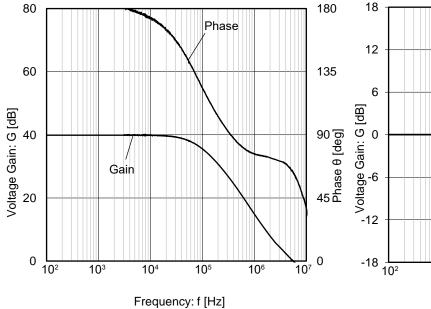


Figure 21. Gain Bandwidth Product vs Ambient Temperature

Figure 22. Phase Margin vs Load Capacitance ($V_S = 5 \text{ V}, R_F = 10 \text{ k}\Omega, G = 40 \text{ dB}$)

Load Capacitance: C_L [pF]



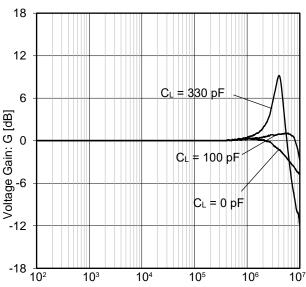


Figure 23. Voltage Gain vs Frequency (Vs = 5 V)

Figure 24. Voltage Gain vs Frequency $(V_S = 5 \text{ V}, G = 0 \text{ dB}, V_{IN} = 180 \text{ mV}_{P-P})$

Frequency: f [Hz]

Application Examples

Voltage Follower

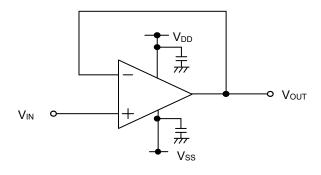


Figure 25. Voltage Follower Circuit

Using this circuit, the output voltage (V_{OUT}) is configured to be equal to the input voltage (V_{IN}). This circuit also stabilizes the output voltage due to high input impedance and low output impedance. Computation for output voltage is shown below.

$$V_{OUT} = V_{IN}$$

oInverting Amplifier

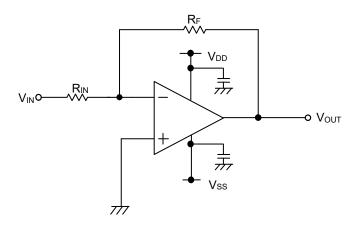


Figure 26. Inverting Amplifier Circuit

For inverting amplifier, input voltage (V_{IN}) is amplified by a voltage gain which depends on the ratio of R_{IN} and R_{F} , and then it outputs phase-inverted voltage. The output voltage is shown in the next expression.

$$V_{OUT} = -\frac{R_F}{R_{IN}} V_{IN}$$

This circuit has input impedance equal to R_{IN}.

oNon-inverting Amplifier

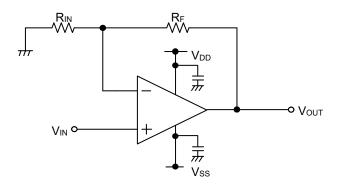


Figure 27. Non-inverting Amplifier Circuit

For non-inverting amplifier, input voltage (V_{IN}) is amplified by a voltage gain, which depends on the ratio of R_{IN} and R_F . The output voltage (V_{OUT}) is in-phase with the input voltage and is shown in the next expression.

$$V_{OUT} = \left(1 + \frac{R_F}{R_{IN}}\right) V_{IN}$$

Effectively, this circuit has high input impedance since its input side is the same as that of the operational amplifier.

I/O Equivalence Circuits

Pin No.	Pin Name	Pin Description	Equivalence Circuit
1 7 8 14	OUT1 OUT2 OUT3 OUT4	Output	1, 7 8,14
2 3 5 6 9 10 12 13	-IN1 +IN1 +IN2 -IN2 -IN3 +IN3 +IN4 -IN4	Input	2, 3, 5, 6 9,10,12,13

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operational Notes - continued

10. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

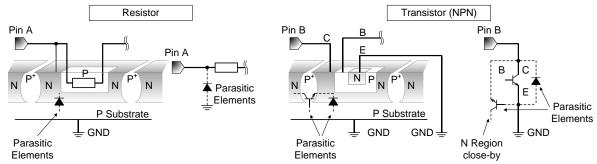
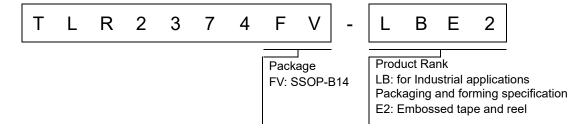


Figure 28. Example of Monolithic IC Structure

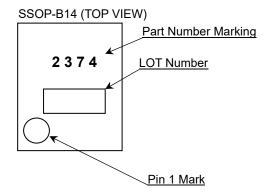
11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

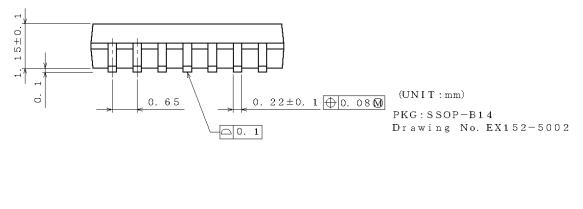
Ordering Information



Marking Diagrams

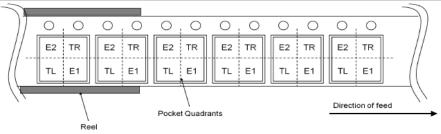


Physical Dimension and Packing Information SSOP-B14 Package Name 5. 0 ± 0 . 2 (Max5. 35 (include. BURR) 14 6. 4 ± 0 . 3MIN 0. 15 ± 0.1





Tape	Embossed carrier tape
Quantity	2500pcs
Direction of feed	E2
	The direction is the pin 1 of product is at the upper left when you hold
	reel on the left hand and you pull out the tape on the right hand



Revision History

Date	Revision	Changes
31.Aug.2023	001	New Release

Notice

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1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA
CLASSIII	CL ACCIII	CLASS II b	CL ACCIII
CLASSIV	CLASSⅢ	CLASSIII	CLASSⅢ

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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

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